

Amendments to the Claims:

This listing of the claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-11 (Canceled)

12. (Currently amended) A plating method for forming a plating film on a conductor layer, which is formed on at least a part of a structural object having a concave-convex pattern on a semiconductor substrate, comprising providing a cathode potential to the conductor layer and supplying a plating solution which electrically connects an anode with the conductor layer,

wherein the plating solution contains 25-75 g/l of copper ion and 0.4 mol/l or more of an organic acid or inorganic acid and

an electric resistor is installed between the conductor layer and the anode; and

the method is carried out at an electrical conductivity of 3 S/m or less.

Claim 13 (Canceled)

14. (Original) The plating method according to claim 12, wherein the organic acid or inorganic acid is sulfuric acid, alkane sulfonic acid, or alkanol sulfonic acid.

15. (Original) The plating method according to claim 12, wherein a copper compound selected from the group consisting of copper sulfate, copper oxide, copper chloride, copper carbonate, copper pyrophosphate, copper alkane sulfonate, copper alkanol sulfonate, and organic acid copper is used as a copper ion source.

16. (Original) The plating method according to claim 12, wherein the organic acid or inorganic acid is sulfuric acid and the copper ion source is copper sulfate.

17. (Original) The plating method according to claim 12, wherein the organic acid or inorganic acid is sulfuric acid, the copper ion source is copper sulfate, and the copper ion concentration is 58 g/l or less.

18. (Original) The plating method according to claim 12, wherein the concave-convex pattern formed on a semiconductor substrate comprises a pattern with a wiring width or via of 0.1 μm or less.

Claims 19-24 (Canceled)